

2SC4656G

Silicon NPN epitaxial planar type

For high-frequency amplification

Complementary to 2SA1791G

■ Features

- High transition frequency f_T
- Small collector output capacitance (Common base, input open circuited) C_{ob}
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	50	V
Collector-emitter voltage (Base open)	V_{CEO}	50	V
Emitter-base voltage (Collector open)	V_{EBO}	5	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	125	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Package

- Code
SSMini3-F3
- Marking Symbol: AM
- Pin Name
 1. Base
 2. Emitter
 3. Collector

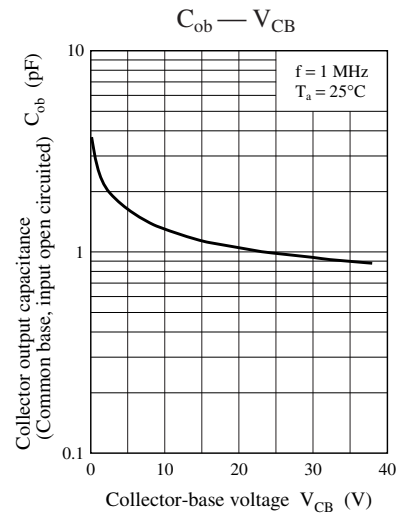
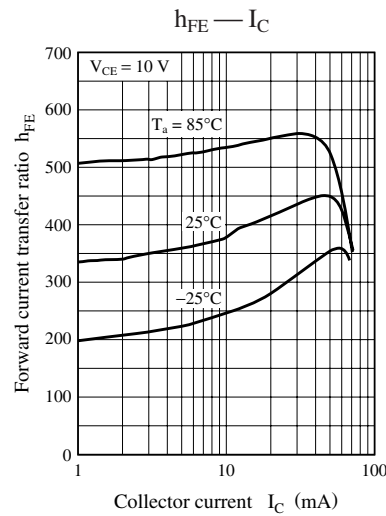
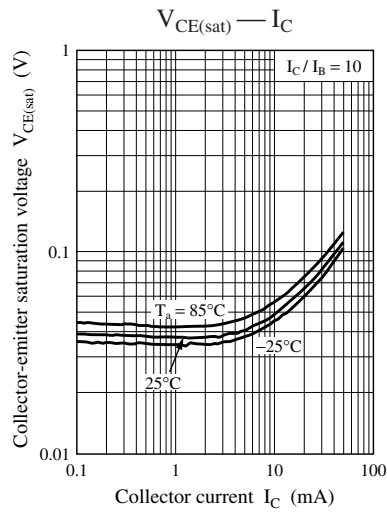
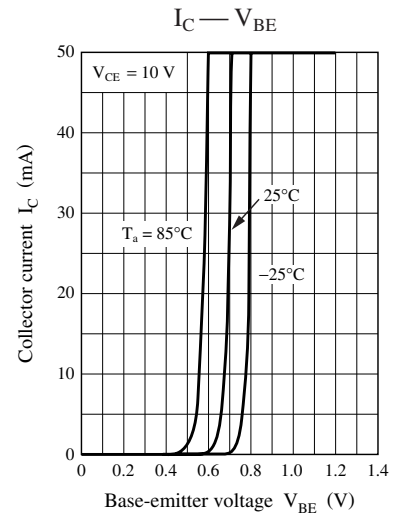
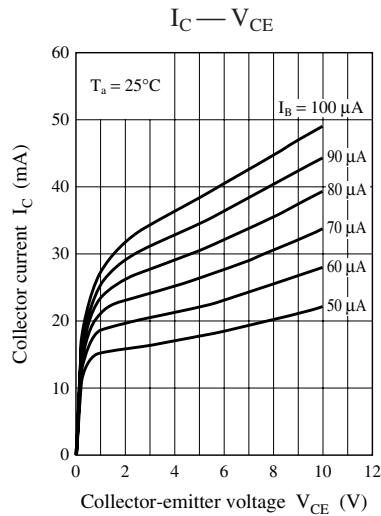
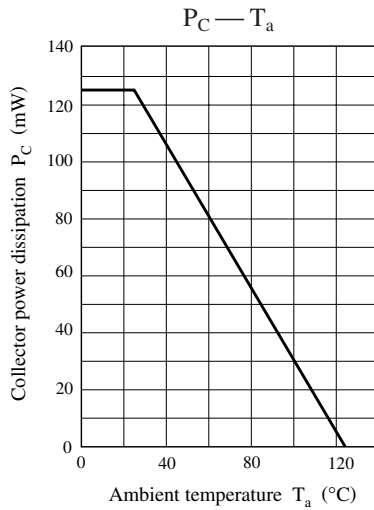
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10\ \mu\text{A}$, $I_E = 0$	50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 1\ \text{mA}$, $I_B = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10\ \mu\text{A}$, $I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 10\ \text{V}$, $I_E = 0$			0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 10\ \text{V}$, $I_B = 0$			100	μA
Forward current transfer ratio *	h_{FE}	$V_{CE} = 10\ \text{V}$, $I_C = 2\ \text{mA}$	200		500	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\ \text{mA}$, $I_B = 1\ \text{mA}$		0.06	0.3	V
Transition frequency	f_T	$V_{CB} = 10\ \text{V}$, $I_E = -2\ \text{mA}$, $f = 200\ \text{MHz}$		250		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 10\ \text{V}$, $I_E = 0$, $f = 1\ \text{MHz}$		1.5		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

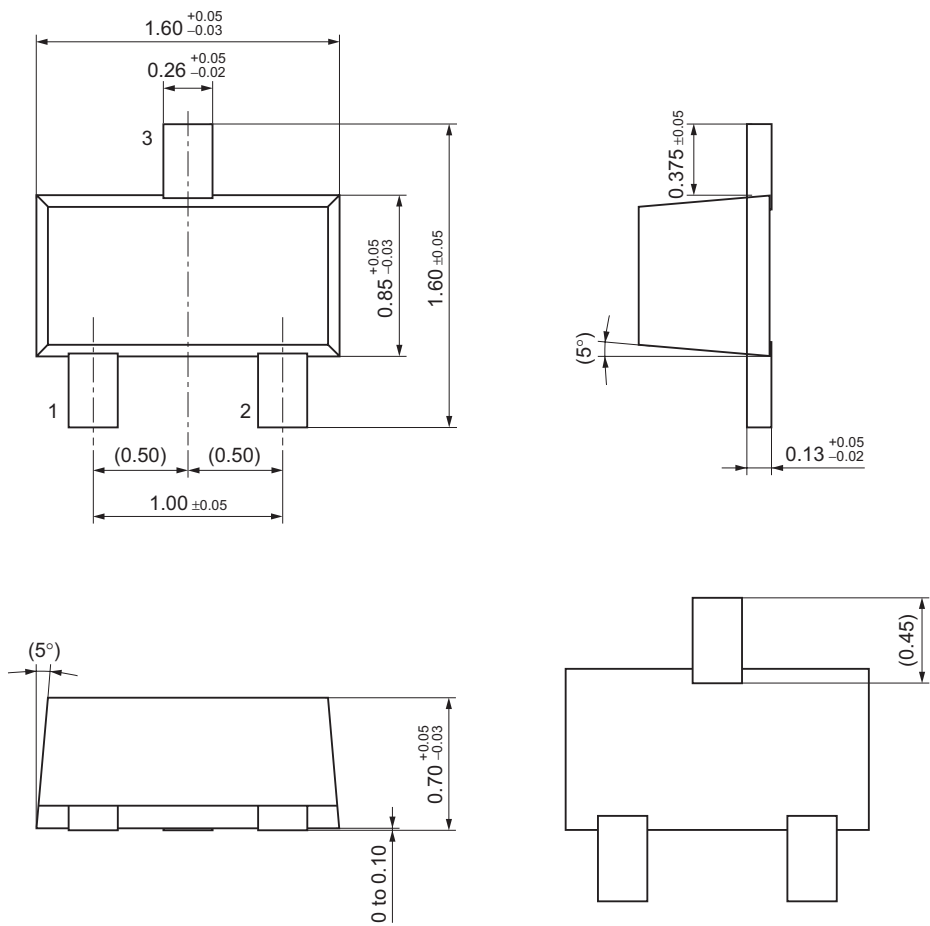
2. *: Rank classification

Rank	Q	R
h_{FE}	200 to 400	250 to 500



SSMini3-F3

Unit: mm



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